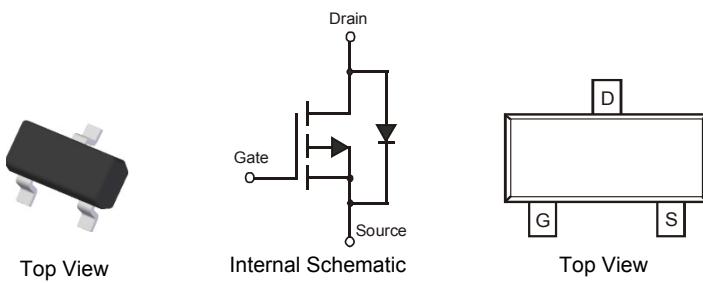


## Features

- Low On-Resistance
  - 60mΩ @  $V_{GS} = -4.5V$
  - 90mΩ @  $V_{GS} = -2.5V$
  - 113mΩ @  $V_{GS} = -1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



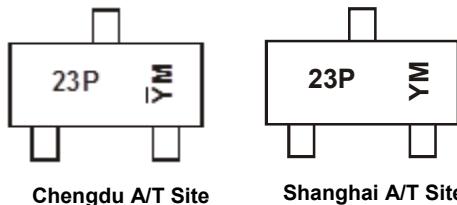
## Ordering Information (Note 4&5)

Part Number	Qualification	Case	Packaging
DMP2305U-7	Standard	SOT23	3000/Tape & Reel
DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/)
5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

## Marking Information



23P = Product Type Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)  
 Y or YM = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015					
Code	W	X	Y	Z	A	B	C					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	$\pm 8$	V
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-4.2 -3.4	A
Pulsed Drain Current (Note 7)			$I_{DM}$	-10	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_D$	1.4	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	-1.0	$\mu\text{A}$	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(\text{th})}$	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	45	60	mΩ	$V_{GS} = -4.5\text{V}, I_D = -4.2\text{A}$
			60	90		$V_{GS} = -2.5\text{V}, I_D = -3.4\text{A}$
			87	113		$V_{GS} = -1.8\text{V}, I_D = -2.0\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	9	—	S	$V_{DS} = -5\text{V}, I_D = -4\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	727	—	pF	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	69	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	64	—	pF	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1.0\text{MHz}$
Gate Resistance	$R_G$	—	23	—	Ω	
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	$Q_g$	—	7.6	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -4\text{V}, I_D = -3.5\text{A}$
Gate-Source Charge	$Q_{gs}$	—	1.4	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	1.2	—	nC	
Turn-On Delay Time	$t_{D(\text{on})}$	—	14.0	—	ns	$V_{DS} = -4\text{V}, V_{GS} = -4.5\text{V}, R_L = 4\Omega, R_G = 6\Omega, I_D = -1\text{A}$
Turn-On Rise Time	$t_r$	—	13.0	—	ns	
Turn-Off Delay Time	$t_{D(\text{off})}$	—	53.8	—	ns	
Turn-Off Fall Time	$t_f$	—	23.2	—	ns	

Notes:

6. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width  $t \leq 10\text{s}$ .
7. Repetitive rating, pulse width limited by junction temperature.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

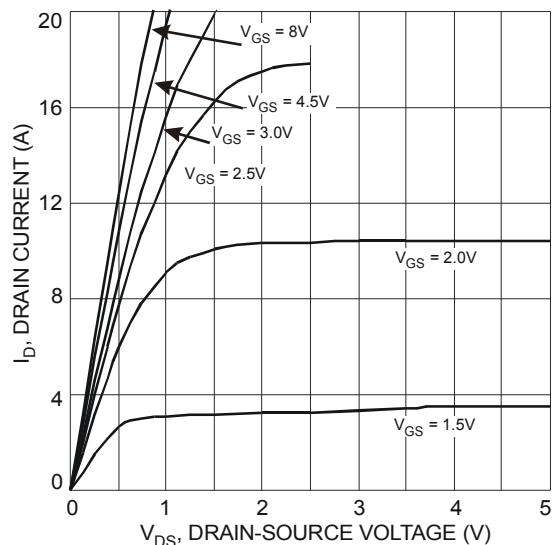


Fig. 1 Typical Output Characteristic

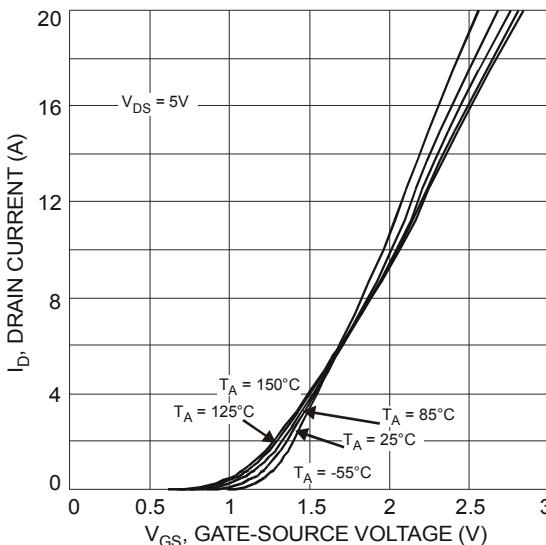


Fig. 2 Typical Transfer Characteristic

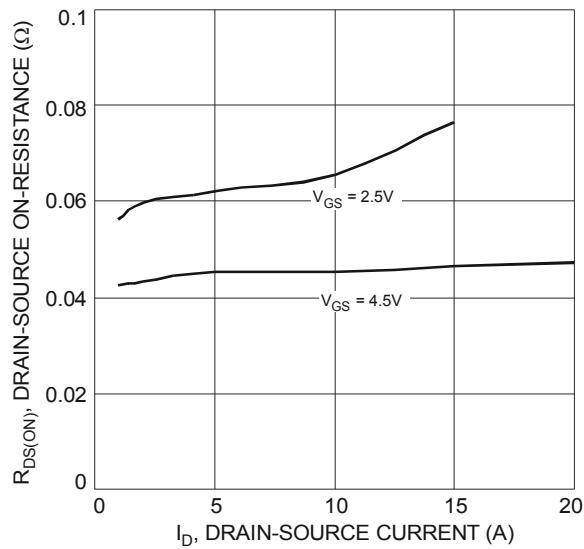


Fig. 3 Typical On-Resistance  
vs. Drain Current and Gate Voltage

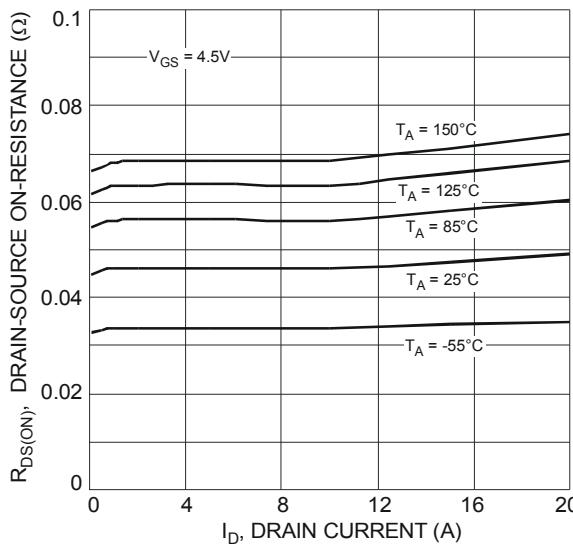


Fig. 4 Typical On-Resistance  
vs. Drain Current and Temperature

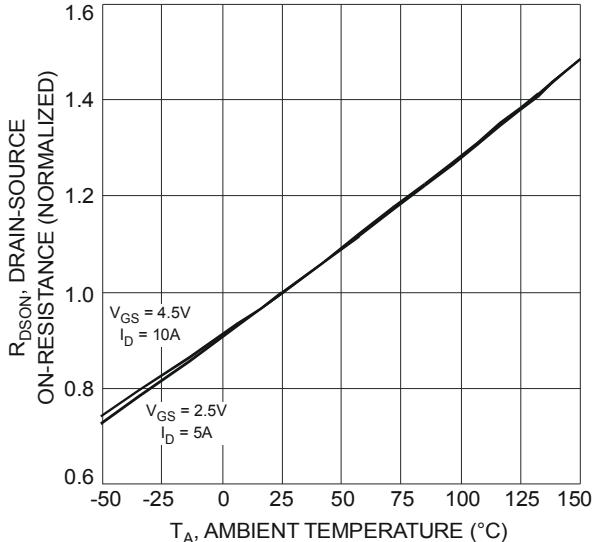


Fig. 5 On-Resistance Variation with Temperature

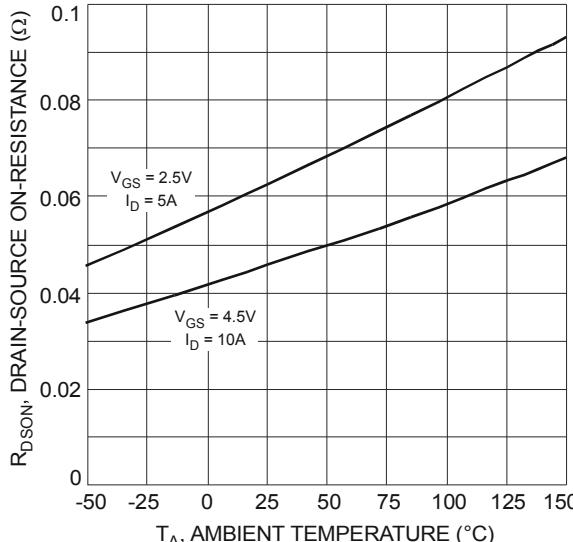


Fig. 6 On-Resistance Variation with Temperature

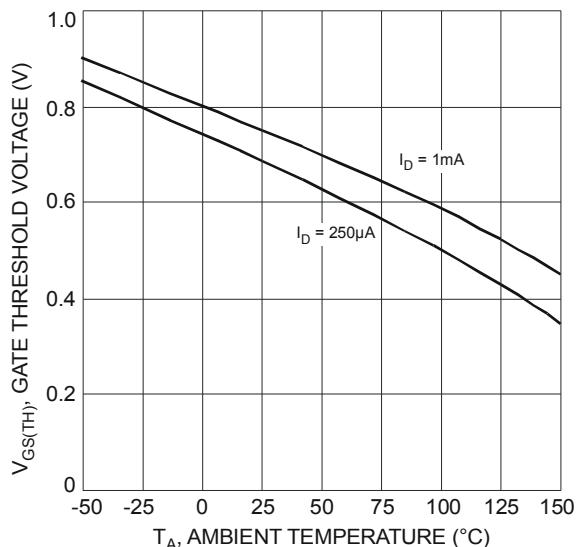


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

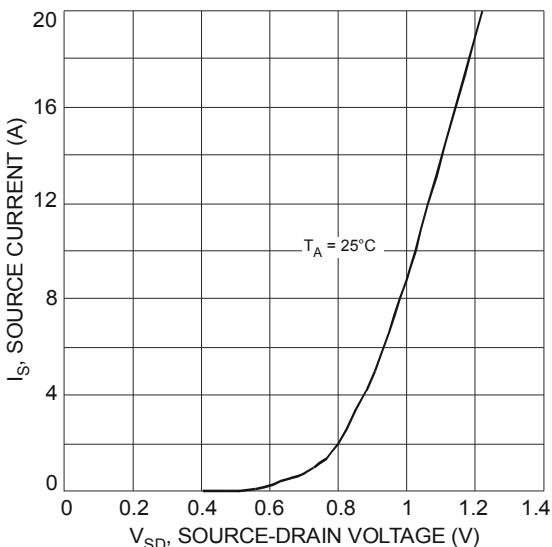


Fig. 8 Diode Forward Voltage vs. Current

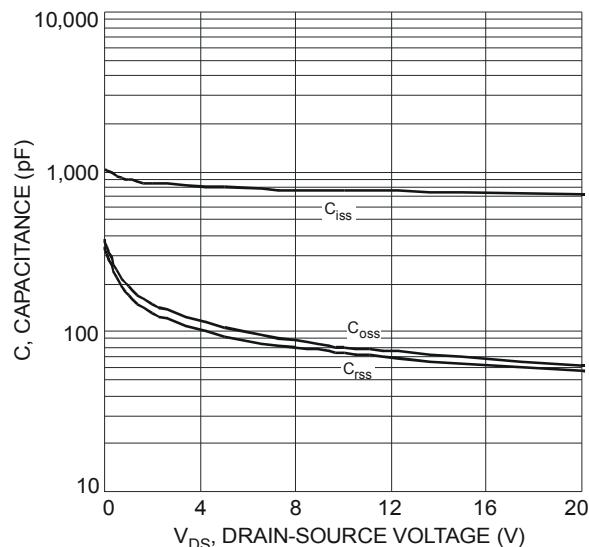


Fig. 9 Typical Total Capacitance

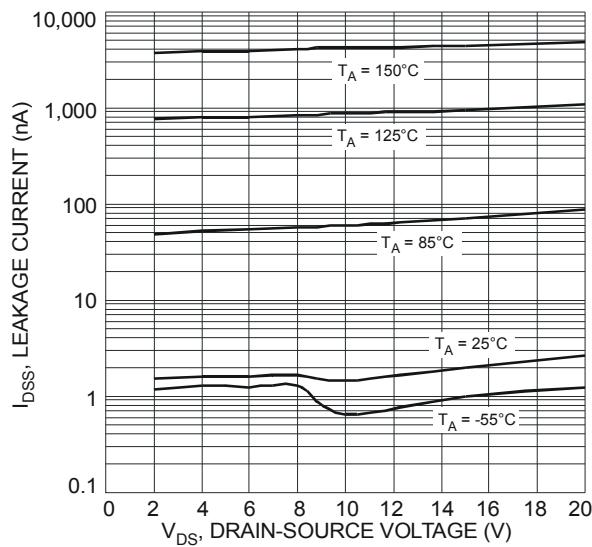


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

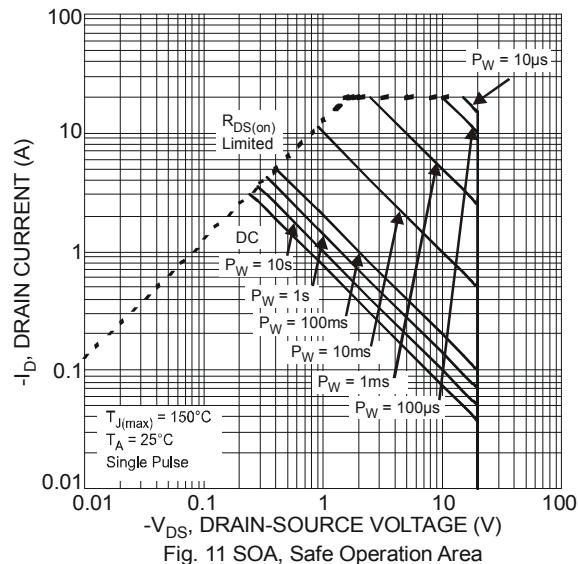


Fig. 11 SOA, Safe Operation Area

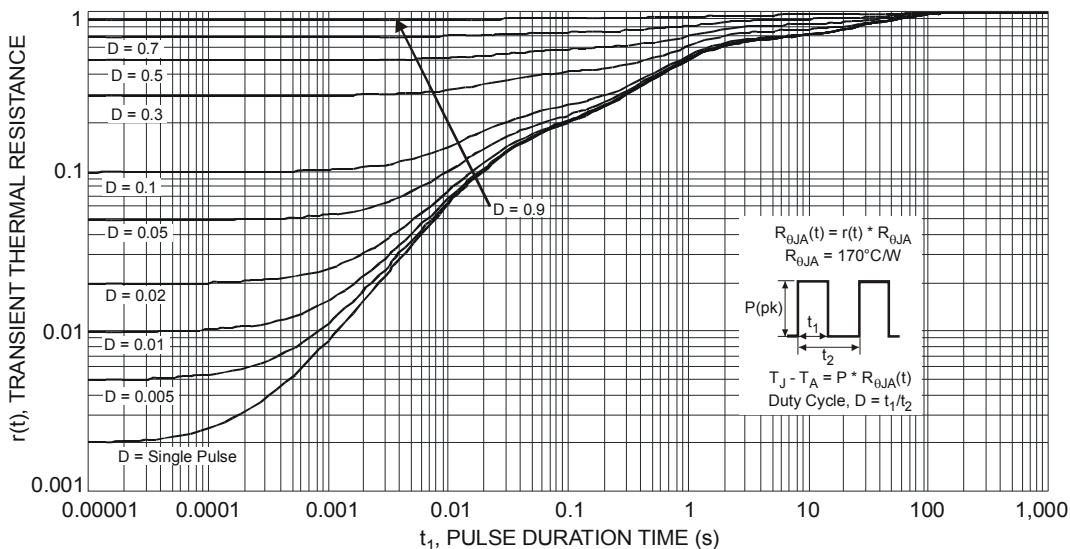
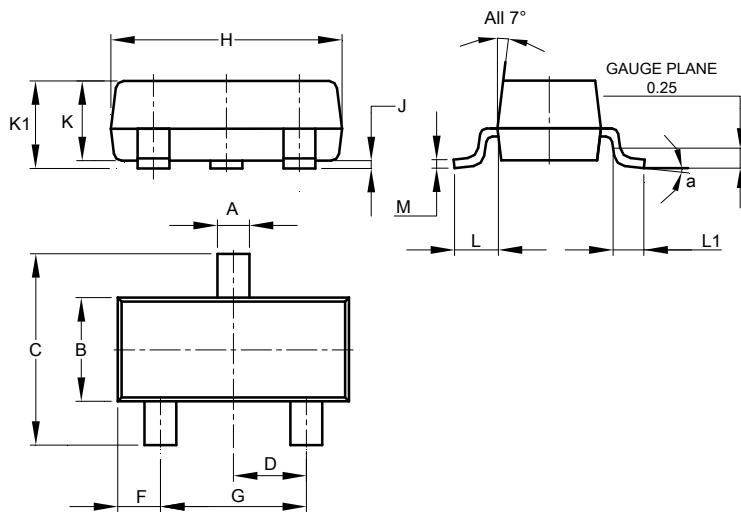


Fig. 12 Transient Thermal Response

## Package Outline Dimensions

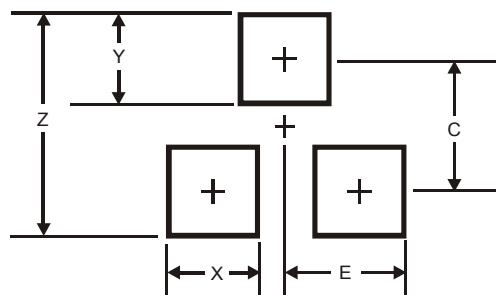
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
$\alpha = 8^\circ$			
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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